

IRF830

N-channel mosfet transistor

◆ Features

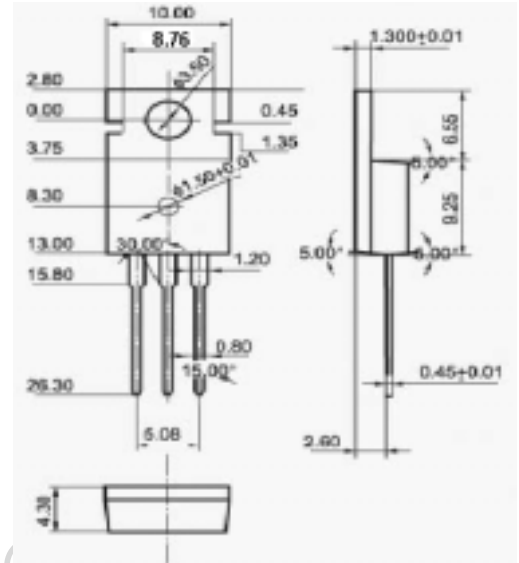
- With TO-220 package
- Simple drive requirements
- Fast switching
- $V_{DSS}=500V$; $R_{DS(ON)} 1.5$; $I_D=4.5A$
- 1.gate 2.drain 3.source

◆ Absolute Maximum Ratings $T_c=25$

SYMBOL	PARAMETER	RATING	UNIT
V_{DSS}	Drain-source voltage ($V_{GS}=0$)	500	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25$	4.5	A
P_{tot}	Total Dissipation@ $T_C=25$	100	W
T_j	Max. Operating Junction temperature	150	
T_{stg}	Storage temperature	-65~150	



1 2 3



TO-220

◆ Electrical Characteristics $T_c=25$

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS}=0$; $I_D=0.25mA$	500		V
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}$; $I_D=0.25mA$	2	4	V
$R_{DS(ON)}$	Drain-source on-stage resistance	$V_{GS}=10V$; $I_D=2.7A$		1.5	
I_{GSS}	Gate source leakage current	$V_{GS}=\pm 20V$; $V_{DS}=0$		± 100	nA
I_{DSS}	Zero gate voltage drain current	$V_{DS}=500V$; $V_{GS}=0$		1.0	μA
V_{SD}	Diode forward voltage	$I_F=4.5A$; $V_{GS}=0$		1.6	V